

OCT 0 4 2007

PATENT

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September 25, 2007

Alexandra Beggs

Date

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Tae H. Kim Attorney Docket No.: 501299.01

Patent No. : US 6,975,552 B2 Serial No. : 10/644,610

Issue Date: December 13, 2005 Filed: August 19, 2003

Title : HYBRID OPEN AND FOLDED DIGIT LINE ARCHITECTURE

REQUEST FOR CERTIFICATE OF CORRECTION

Certificate

OCT 0 9 2007

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

of Correction

Sir:

A Certificate of Correction under 35 U.S.C. § 254 is respectfully requested for the above-identified patent in order to correct Patent and Trademark Office errors made during the printing of the patent. The changes in the patent needed to correct the errors are as follows:

Column, Line	Reads	Should Read
Item (57), Line 3	"and an open digit line"	and open digit line
Column 1, Lines 45, 50 and 52	"complimentary"	complementary
Column 2, Line 40	"pair is surrounded"	pair being surrounded
Column 4, Line 30	"to which portion of a digit line memory cells are"	to which portions of a digit line of memory cells are
Column 4, Line 41	"aspects of a open digit line"	aspects of an open digit line

Column 4, Line 64	"array 10, thus, coupling"	array 10, thus coupling
Column 5, Line 57	"memory arrays, thus,"	memory arrays, thus
Column 5, Line 59	"to active column 50, 80"	to active columns 50, 80
Column 6, Line 27	"but are instead, shifted"	but are instead shifted
Column 6, Line 41	"are desired. For example,"	are desired; for example,
Column 6, Line 66	"MDL portion 156. virtue of the data state stored by the"	MDL portion 156. Consequently, the voltage of the digit line will be altered from the precharge voltage by virtue of the data state stored by the
Column 7, Line 38	"of the memory arrays 202a, 202b is a respective row various"	of the memory arrays 202a, 202b is a respective row address latch 226, which stores the row address, and a row decoder 228, which applies various
Column 14, Line 21	"cells of the colunm"	cells of the column

The above errors for which correction is requested under 35 U.S.C. § 254 were made in the printing of the patent or in the original application. The errors are considered sufficiently important to justify the processing of a Certificate of Correction under 35 U.S.C. § 254. A Form PTO-1050, in duplicate, is enclosed herewith.

The Commissioner is hereby authorized to charge payment of any fees associated with this communication to Deposit Account No. 50-1266. A duplicate copy of this sheet is enclosed.

Favorable consideration of this Request is respectfully requested.

Respectfully submitted,

Date: Letterber 24, 2007

By: Edward W. Bulchis, Reg. No. 26,847

Customer No. 27,076 Dorsey & Whitney LLP 1420 Fifth Avenue, Suite 3400 Seattle, WA 98101 (206) 903-8785

Attorney for Applicant(s)

EWB:tdp

Enclosures:

Postcard Form PTO-1050 (+ copy)

501299.01 req cert correct

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO.

US 6,975,552 B2

DATED

December 13, 2005

INVENTOR(S)

Tae H. Kim

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Column 6, Line 41	"are desired. For example,"	are desired; for example, OCT © 2007
Column 6, Line 66	"MDL portion 156.	WIDE portion 150.
	virtue of the data state	Consequently, the voltage
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		altered from the precharge
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	" O.1	data state stored by the
Column 7, Line 38	"of the memory arrays	of the memory arrays
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address, and a row decoder 228 which applies various-Column 14, Line 21 "cells of the column" --cells of the column--

MAILING ADDRESS OF SENDER:

Patent No. <u>US 6,975,552 B2</u>

DORSEY & WHITNEY LLP 1420 Fifth Avenue, Suite 3400 Seattle, Washington 98101

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FORM PTO-1050 (REV. 3-82)

501299.01 PTO 1050

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